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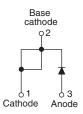
Ultrafast Rectifier, 15 A Fred Pt®





TO-220 FULL-PAK

TO-220AC





VS-15ETH06PbF VS-15ETH06-N3

VS-15ETH06FPPbF VS-15ETH06FP-N3

PRODUCT SUMMARY								
Package	TO-220AC, TO-220FP							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	2.2 V							
t _{rr} typ.	22 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single die center tap module
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V _{RRM}		600	V					
Average rectified forward current	I	T _C = 140 °C	15						
Average rectilied forward current	I _{F(AV)}	T _C = 80 °C (FULL-PAK)	15						
Non-repetitive peak surge current	1	T _J = 25 °C	120	А					
Non-repetitive peak surge current	IFSM	T _J = 25 °C (FULL-PAK)	180						
Peak repetitive forward current	I _{FM}		30						
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-					
Forward voltage	V _F	I _F = 15 A	-	1.8	2.2	V				
		I _F = 15 A, T _J = 150 °C	-	1.3	1.6					
	I _R	$V_R = V_R$ rated	-	0.2	50					
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	30	500	μA				
Junction capacitance	CT	V _R = 600 V	-	20	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

Revision: 02-Jan-12

Document Number: 94002

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(e3) RoHS

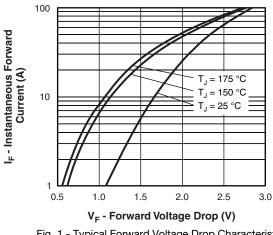
HALOGEN FREE Available

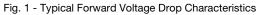
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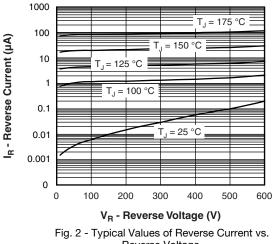
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DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		22	30				
Reverse recovery time	+	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = 100$	0 A/µs, V _R = 30 V	-	28	35	20			
neverse recovery time	t _{rr}	T _J = 25 °C		-	29	-	ns			
		T _J = 125 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 390 V	-	75	-				
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.5	-	А			
Feak recovery current		T _J = 125 °C		-	7	-				
	Q _{rr}	T _J = 25 °C		-	57	-	nC			
Reverse recovery charge		T _J = 125 °C		-	300	-	no			
Reverse recovery time	t _{rr}		I _F = 15 A	-	51	-	ns			
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 800 A/µs	-	20	-	А			
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	580	-	nC			

THERMAL MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C				
Thermal resistance,	D		-	1.0	1.3					
junction to case (FULL-PAK)	R _{thJC}		-	3.0	3.5					
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	.5 -					
\A/-:			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking davias		Case style TO-220AC	15ETH06							
Marking device		Case style TO-220 FULL-PAK	15ETH06FP							







Reverse Voltage

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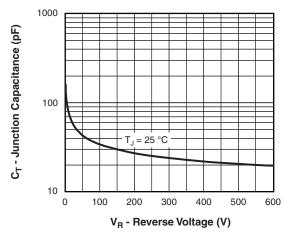


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

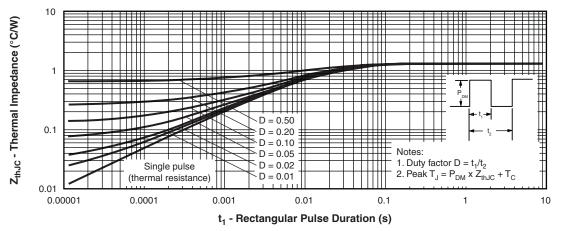


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

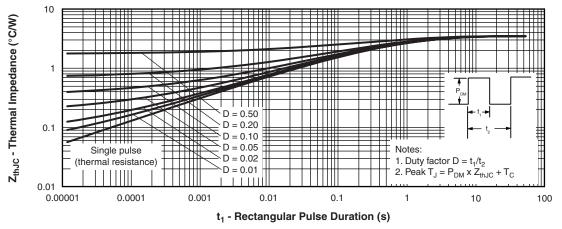
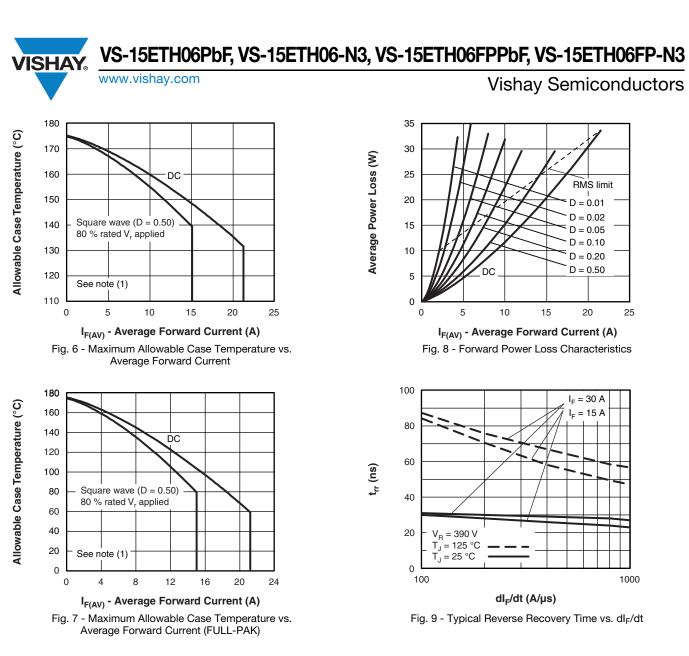


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

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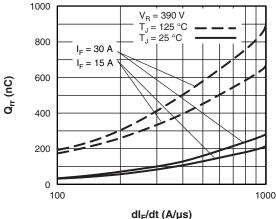


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}/D$) (see fig. 8); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = Rated V_R

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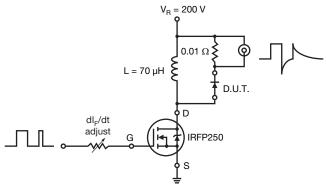
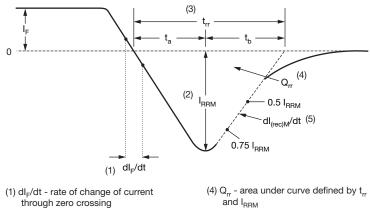


Fig. 11 - Reverse Recovery Parameter Test Circuit

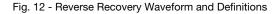


$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(2) I_{RRM} - peak reverse recovery current

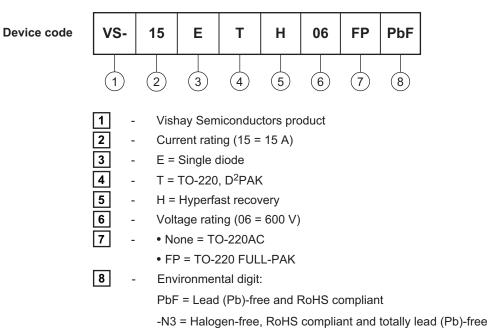
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-15ETH06PbF	50	1000	Antistatic plastic tube							
VS-15ETH06-N3	50	1000	Antistatic plastic tube							
VS-15ETH06FPPbF	50	1000	Antistatic plastic tube							
VS-15ETH06FP-N3	50	1000	Antistatic plastic tube							

LINKS TO RELATED DOCUMENTS								
Dimensions	TO-220AC	www.vishay.com/doc?95221						
Dimensions	TO-220FP	www.vishay.com/doc?95005						
	TO-220ACPbF	www.vishay.com/doc?95224						
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068						
Part marking information	TO-220FPPbF	www.vishay.com/doc?95009						
	TO-220FP-N3	www.vishay.com/doc?95440						

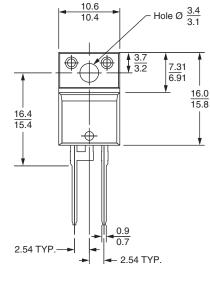
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Outline Dimensions

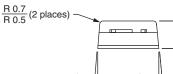
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DIMENSIONS in millimeters

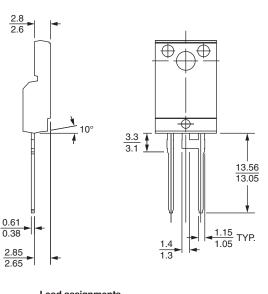


 $\frac{4.8}{4.6}$

 $5^{\circ} \pm 0.5^{\circ}$



 $5^{\circ} \pm 0.5^{\circ}$



Lead assignments Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220 FULL-PAK



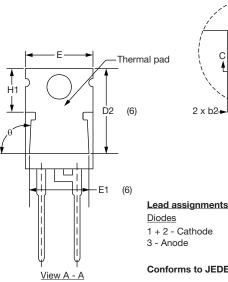
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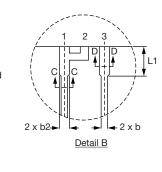
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIMETERS INCHES NOTES	SYMBOL	MILLIN	IETERS	INCHES		NOTES				
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040		e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4	H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068		L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4	L1	3.32	3.82	0.131	0.150	2
С	0.36	0.61	0.014	0.024		L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4	L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3	ØΡ	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355		Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6	θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6						

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

Document Number: 95221 Revision: 07-Mar-11

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